

NL17SH125

Non-Inverting 3-State Buffer

The NL17SH125 MiniGate™ is an advanced high-speed CMOS non-inverting buffer in ultra-small footprint.

The NL17SH125 requires the 3-state control input (\overline{OE}) to be set High to place the output in the high impedance state.

The NL17SH125 input structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

Features

- High Speed: $t_{PD} = 3.8 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1.0 \mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- These are Pb-Free and Halide-Free Devices

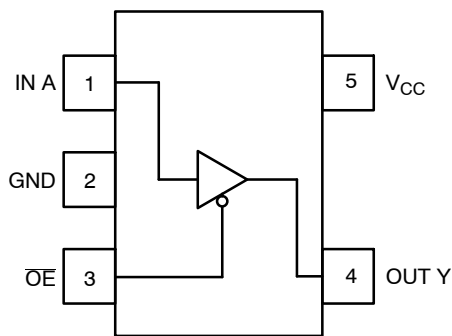


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



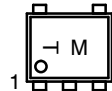
ON Semiconductor®

<http://onsemi.com>

MARKING DIAGRAM



**SOT-953
CASE 527AE**



T = Specific Device Code
(Rotated 90°)
M = Month Code

PIN ASSIGNMENT

1	IN A
2	GND
3	\overline{OE}
4	OUT Y
5	V_{CC}

FUNCTION TABLE

Input A	Input \overline{OE}	Output Y
L	L	L
H	L	H
X	H	Z

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NL17SH125

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V	
V _{IN}	DC Input Voltage	-0.5 to +7.0	V	
V _{OUT}	DC Output Voltage	-0.5 to V _{CC} + 0.5	V	
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND, V _{OUT} > V _{CC}	±20	mA
I _{OUT}	DC Output Source/Sink Current		±12.5	mA
I _{CC}	DC Supply Current per Supply Pin		±25	mA
I _{GND}	DC Ground Current per Ground Pin		±25	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T _J	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>3000 >150 N/A	V
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
2. Tested to EIA/JESD22-A114-A.
3. Tested to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	1.65	5.5	V
V _{IN}	Digital Input Voltage	0.0	5.5	V
V _{OUT}	Output Voltage	0.0	V _{CC}	V
T _A	Operating Temperature Range	-55	+125	°C
Δt / ΔV	Input Transition Rise or Fall Rate	V _{CC} = 3.3 V ± 0.3 V V _{CC} = 5.0 V ± 0.5 V	0 100 20	ns/V

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		-55°C to 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	High-Level Input Voltage		1.65 to 2.0	0.75 x V _{CC}			0.75 x V _{CC}				V
			2.3 to 5.5	0.70 x V _{CC}			0.70 x V _{CC}				
V _{IL}	Low-Level Input Voltage		1.65 to 2.0			0.25 x V _{CC}		0.25 x V _{CC}		0.25 x V _{CC}	V
			2.3 to 5.5			0.30 x V _{CC}		0.30 x V _{CC}		0.30 x V _{CC}	
V _{OH}	High-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Low-Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Input Leakage Current	0 ≤ V _{IN} ≤ 5.5 V	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Quiescent Supply Current	0 ≤ V _{IN} ≤ V _{CC}	5.5			1.0		10		40	μA
I _{OZ}	3-State Leakage Current	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND	0.0			±0.25		±2.5		±2.5	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	V _{CC} (V)	Test Conditions	T _A = 25°C			T _A ≤ 85°C		-55°C to 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, A to Y	3.0 to 3.6	C _L = 15 pF C _L = 50 pF		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
		4.5 to 5.5	C _L = 15 pF C _L = 50 pF		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Y	3.0 to 3.6	C _L = 15 pF C _L = 50 pF		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
		4.5 to 5.5	C _L = 15 pF C _L = 50 pF		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t _{PLZ} , t _{PHZ}	Output Enable Time, OE to Y	3.0 to 3.6	C _L = 15 pF C _L = 50 pF		6.5 8.0	9.7 13.2	1.0 1.0	11.5 15.0		14.5 18.5	ns
		4.5 to 5.5	C _L = 15 pF C _L = 50 pF		4.8 7.0	6.8 8.8	1.0 1.0	8.0 10		10.0 12.0	
C _{IN}	Input Capacitance				5.5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (Note 6)	5.0			11						pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

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ORDERING INFORMATION

Device	Package	Shipping†
NL17SH125P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

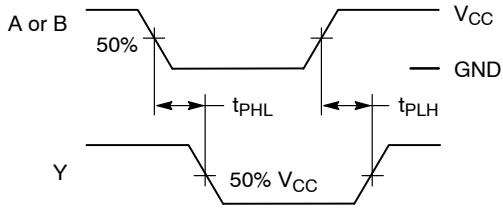


Figure 3. Switching Waveform

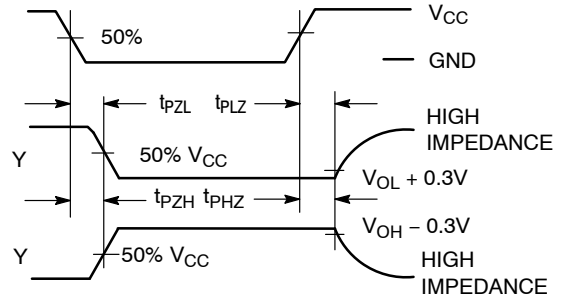
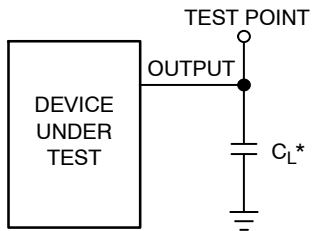
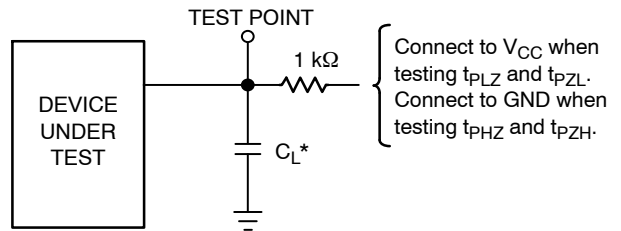


Figure 4.



*Includes all probe and jig capacitance.

Figure 5. Test Circuit



*Includes all probe and jig capacitance.

Figure 6. Test Circuit

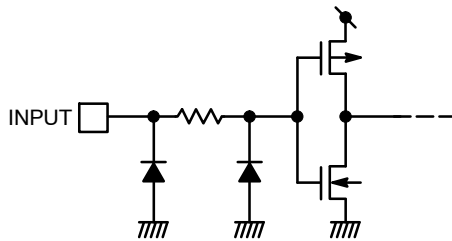


Figure 7. Input Equivalent Circuit

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SOT-953 CASE 527AE ISSUE E

DATE 02 AUG 2011



TOP VIEW



SIDE VIEW



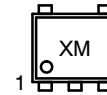
BOTTOM VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H _E	0.95	1.00	1.05
L	0.175 REF		
L2	0.05	0.10	0.15
L3	---	---	0.15

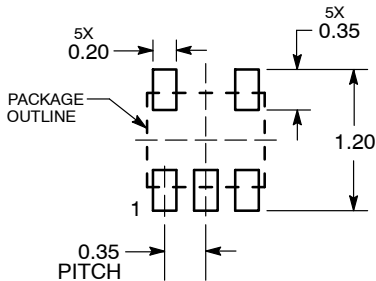
GENERIC MARKING DIAGRAM*



- X = Specific Device Code
- M = Month Code

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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